



#### Welcome to E-XFL.COM

#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

Product Status	Active
Core Processor	ARM® Cortex®-M3
Core Size	32-Bit Single-Core
Speed	32MHz
Connectivity	I <sup>2</sup> C, IrDA, LINbus, SPI, UART/USART, USB
Peripherals	Brown-out Detect/Reset, Cap Sense, DMA, I <sup>2</sup> S, POR, PWM, WDT
Number of I/O	109
Program Memory Size	384KB (384K x 8)
Program Memory Type	FLASH
EEPROM Size	12K x 8
RAM Size	48K x 8
Voltage - Supply (Vcc/Vdd)	1.8V ~ 3.6V
Data Converters	A/D 40x12b; D/A 2x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	132-UFBGA
Supplier Device Package	132-UFBGA (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32l151qdh6tr

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

# 2.1 Device overview

#### Table 2. Ultra-low-power STM32L151xD and STM32L152xD device features and peripheral counts

Perij	pheral	STM32L15xRD	STM32L15xVD	STM32L15xQD	STM32L15xZD					
Flash (Kbytes	;)		38	34						
Data EEPROM	l (Kbytes)		1	2						
RAM (Kbytes)			4	8						
FSMC		No	multiplexed only	Ye	es					
	32 bit			I						
Timers	General- purpose		6	3						
	Basic		2	2						
	SPI		8(3) <sup>(1)</sup>							
	l <sup>2</sup> S		2	2						
Communi- cation interfaces	l <sup>2</sup> C		2	2						
	USART		Ę	5						
	USB			l						
	SDIO			l						
GPIOs		51	83	109	115					
Operation am	plifiers		3	3						
12-bit synchro Number of ch	onized ADC annels	1 21	1 25	1 40	1 40					
12-bit DAC Number of ch	annels			2						
LCD (STM32L	152xx devices	1		1						
COM x SEG		4x32 or 8x28		4x44 or 8x40						
Comparators				2						
Capacitive se	nsing channels	2	3	33	34					
Max. CPU free	quency	32 MHz								
Operating vol	tage	1.8 V to 3.6	6 V (down to 1.65 V a 1.65 V to 3.6 V wi	t power-down) with E thout BOR option	BOR option					



## 3.5 Low-power real-time clock and backup registers

The real-time clock (RTC) is an independent BCD timer/counter. Dedicated registers contain the sub-second, second, minute, hour (12/24 hour), week day, date, month, year, in BCD (binary-coded decimal) format. Correction for 28, 29 (leap year), 30, and 31 day of the month are made automatically. The RTC provides two programmable alarms and programmable periodic interrupts with wakeup from Stop and Standby modes.

The programmable wakeup time ranges from 120 µs to 36 hours.

The RTC can be calibrated with an external 512 Hz output, and a digital compensation circuit helps reduce drift due to crystal deviation.

The RTC can also be automatically corrected with a 50/60Hz stable powerline.

The RTC calendar can be updated on the fly down to sub second precision, which enables network system synchronization.

A time stamp can record an external event occurrence, and generates an interrupt.

There are thirty-two 32-bit backup registers provided to store 128 bytes of user application data. They are cleared in case of tamper detection.

Three pins can be used to detect tamper events. A change on one of these pins can reset backup register and generate an interrupt. To prevent false tamper event, like ESD event, these three tamper inputs can be digitally filtered.

# 3.6 GPIOs (general-purpose inputs/outputs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions, and can be individually remapped using dedicated AFIO registers. All GPIOs are high current capable. The alternate function configuration of I/Os can be locked if needed following a specific sequence in order to avoid spurious writing to the I/O registers. The I/O controller is connected to the AHB with a toggling speed of up to 16 MHz.

#### External interrupt/event controller (EXTI)

The external interrupt/event controller consists of 24 edge detector lines used to generate interrupt/event requests. Each line can be individually configured to select the trigger event (rising edge, falling edge, both) and can be masked independently. A pending register maintains the status of the interrupt requests. The EXTI can detect an external line with a pulse width shorter than the Internal APB2 clock period. Up to 115 GPIOs can be connected to the 16 external interrupt lines. The 8 other lines are connected to RTC, PVD, USB, comparator events or capacitive sensing acquisition.



operate. This acquisition is managed directly by the GPIOs, timers and analog I/O groups (see *Section 3.15: System configuration controller and routing interface*).

Reliable touch sensing functionality can be quickly and easily implemented using the free STM32L1xx STMTouch touch sensing firmware library.

# 3.17 Timers and watchdogs

The ultra-low-power STM32L151xD and STM32L152xD devices include seven generalpurpose timers, two basic timers, and two watchdog timers.

*Table 6* compares the features of the general-purpose and basic timers.

Timer	Counter resolution	Counter type	Prescaler factor	DMA request generation	Capture/compare channels	Complementary outputs
TIM2, TIM3, TIM4	16-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM5	32-bit	Up, down, up/down	Any integer between 1 and 65536	Yes	4	No
TIM9	16-bit	Up, down, up/down	Any integer between 1 and 65536	No	2	No
TIM10, TIM11	16-bit	Up	Any integer between 1 and 65536	No	1	No
TIM6, TIM7	16-bit	Up	Any integer between 1 and 65536	Yes	0	No

 Table 6. Timer feature comparison

# 3.17.1 General-purpose timers (TIM2, TIM3, TIM4, TIM5, TIM9, TIM10 and TIM11)

There are seven synchronizable general-purpose timers embedded in the STM32L151xD and STM32L152xD devices (see *Table 6* for differences).

## TIM2, TIM3, TIM4, TIM5

TIM2, TIM3, TIM4 are based on 16-bit auto-reload up/down counter. TIM5 is based on a 32bit auto-reload up/down counter. They include a 16-bit prescaler. They feature four independent channels each for input capture/output compare, PWM or one-pulse mode output. This gives up to 16 input captures/output compares/PWMs on the largest packages.

TIM2, TIM3, TIM4, TIM5 general-purpose timers can work together or with the TIM10, TIM11 and TIM9 general-purpose timers via the Timer Link feature for synchronization or event chaining. Their counter can be frozen in debug mode. Any of the general-purpose timers can be used to generate PWM outputs.

TIM2, TIM3, TIM4, TIM5 all have independent DMA request generation.

These timers are capable of handling quadrature (incremental) encoder signals and the digital outputs from 1 to 3 hall-effect sensors.

DocID022027 Rev 11



#### 3.18.2 Universal synchronous/asynchronous receiver transmitter (USART)

The three USART and two UART interfaces are able to communicate at speeds of up to 4 Mbit/s. They support IrDA SIR ENDEC and have LIN Master/Slave capability. The three USARTs provide hardware management of the CTS and RTS signals and are ISO 7816 compliant.

All USART/UART interfaces can be served by the DMA controller.

## 3.18.3 Serial peripheral interface (SPI)

Up to three SPIs are able to communicate at up to 16 Mbits/s in slave and master modes in full-duplex and half-duplex communication modes. The 3-bit prescaler gives 8 master mode frequencies and the frame is configurable to 8 bits or 16 bits. The hardware CRC generation/verification supports basic SD Card/MMC modes.

The SPIs can be served by the DMA controller.

## 3.18.4 Inter-integrated sound (I<sup>2</sup>S)

Two standard I2S interfaces (multiplexed with SPI2 and SPI3) are available. They can operate in master or slave mode, and can be configured to operate with a 16-/32-bit resolution as input or output channels. Audio sampling frequencies from 8 kHz up to 192 kHz are supported. When either or both of the I2S interfaces is/are configured in master mode, the master clock can be output to the external DAC/CODEC at 256 times the sampling frequency.

The I2Ss can be served by the DMA controller.

#### 3.18.5 SDIO

An SD/SDIO/MMC host interface is available, that supports MultiMediaCard System Specification Version 4.2 in three different databus modes: 1-bit (default), 4-bit and 8-bit.

The interface allows data transfer at up to 24 MHz in 8-bit mode, and is compliant with the SD Memory Card Specification Version 2.0.

The SDIO Card Specification Version 2.0 is also supported with two different databus modes: 1-bit (default) and 4-bit.

The current version supports only one SD/SDIO/MMC4.2 card at any one time and a stack of MMC4.1 or previous.

In addition to SD/SDIO/MMC, this interface is fully compliant with the CE-ATA digital protocol Rev1.1.

## 3.18.6 Universal serial bus (USB)

The STM32L151xD and STM32L152xD devices embed a USB device peripheral compatible with the USB full-speed 12 Mbit/s. The USB interface implements a full-speed (12 Mbit/s) function interface. It has software-configurable endpoint setting and supports suspend/resume. The dedicated 48 MHz clock is generated from the internal main PLL (the clock source must use a HSE crystal oscillator).



	F	Pins							Pin functior	IS
LQFP144	UFBGA132	LQFP100	LQFP64	WLCSP64	Pin name	Pin Type <sup>(1)</sup>	I / O structure	Main function <sup>(2)</sup> (after reset)	Alternate functions	Additional functions
14	F3	-	-	-	PF4	I/O	FT	PF4	FSMC_A4	-
15	F4	I	-	-	PF5	I/O	FT	PF5	FSMC_A5	-
16	F2	10	-	-	$V_{SS_5}$	S	-	$V_{SS_5}$	-	-
17	G2	11	-	-	$V_{DD_5}$	S	-	$V_{DD_5}$	-	-
18	G3	1	-	-	PF6	I/O	FT	PF6	TIM5_CH1/TIM5_ETR	ADC_IN27
19	G4	-	-	-	PF7	I/O	FT	PF7	TIM5_CH2	ADC_IN28/ COMP1_INP
20	H4	-	-	-	PF8	I/O	FT	PF8	TIM5_CH3	ADC_IN29/ COMP1_INP
21	J6	-	-	-	PF9	I/O	FT	PF9	TIM5_CH4	ADC_IN30/ COMP1_INP
22	-	-	-	-	PF10	I/O	FT	PF10	-	ADC_IN31/ COMP1_INP
23	F1	12	5	D8	PH0- OSC_IN <sup>(5)</sup>	I/O	тс	PH0	-	OSC_IN
24	G1	13	6	D7	PH1- OSC_OUT <sup>(5)</sup>	I/O	тс	PH1	-	OSC_OUT
25	H2	14	7	C7	NRST	I/O	RST	NRST	-	-
26	H1	15	8	E8	PC0	I/O	FT	PC0	LCD_SEG18	ADC_IN10/ COMP1_INP
27	J2	16	9	F8	PC1	I/O	FT	PC1	LCD_SEG19	ADC_IN11/ COMP1_INP OPAMP3_VINP
28	-	17	10	D6	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP OPAMP3_VINM
-	J3	-	-	-	PC2	I/O	FT	PC2	LCD_SEG20	ADC_IN12/ COMP1_INP
-	K1	-	-	-	OPAMP3_VI NM	Ι	-	OPAMP3 _VINM	-	-
29	K2	18	11	F7	PC3	I/O	тс	PC3	LCD_SEG21	ADC_IN13/ COMP1_INP/ OPAMP3_VOUT
30	J1	19	12	E7	V <sub>SSA</sub>	S	-	V <sub>SSA</sub>	-	-

## Table 8. STM32L151xD and STM32L152xD pin definitions (continued)



	F	Pins							Pin function	S
LQFP144	UFBGA132	LQFP100	LQFP64	WLCSP64	Pin name	Pin Type <sup>(1)</sup>	I / O structure	Main function <sup>(2)</sup> (after reset)	Alternate functions	Additional functions
79	J12	57	-	-	PD10	I/O	FT	PD10	USART3_CK/LCD_SEG30/ FSMC_D15	-
80	J11	58	-	-	PD11	I/O	FT	PD11	USART3_CTS/LCD_SEG31 /FSMC_A16	-
81	J10	59	-	-	PD12	I/O	FT	PD12	TIM4_CH1/USART3_RTS/ LCD_SEG32/ FSMC_A17	-
82	H12	60	-	-	PD13	I/O	FT	PD13	TIM4_CH2/LCD_SEG33/ FSMC_A18	-
83	-	-	-	-	V <sub>SS_8</sub>	S	-	V <sub>SS_8</sub>	-	-
84	-	-	-	-	V <sub>DD_8</sub>	S	-	V <sub>DD_8</sub>	-	-
85	H11	61	-	-	PD14	I/O	FT	PD14	TIM4_CH3/LCD_SEG34/ FSMC_D0	-
86	H10	62	-	-	PD15	I/O	FT	PD15	TIM4_CH4/LCD_SEG35 /FSMC_D1	-
87	G10	-	-	-	PG2	I/O	FT	PG2	FSMC_A12	ADC_IN10b
88	F9	-	-	-	PG3	I/O	FT	PG3	FSMC_A13	ADC_IN11b
89	F10	-	-	-	PG4	I/O	FT	PG4	FSMC_A14	ADC_IN12b
90	E9	-	-	-	PG5	I/O	FT	PG5	FSMC_A15	-
91	-	-	-	-	PG6	I/O	FT	PG6	-	-
92	-	-	-	-	PG7	I/O	FT	PG7	-	-
93	-	-	-	-	PG8	I/O	FT	PG8	-	-
94	F6	-	-	-	V <sub>SS_9</sub>	S		V <sub>SS_9</sub>	-	-
95	G6	-	-	-	V <sub>DD_9</sub>	S		V <sub>DD_9</sub>	-	-
96	E12	63	37	E1	PC6	I/O	FT	PC6	TIM3_CH1/I2S2_MCK/ LCD_SEG24/SDIO_D6	-
97	E11	64	38	E2	PC7	I/O	FT	PC7	TIM3_CH2/I2S3_MCK/ LCD_SEG25/SDIO_D7	-
98	E10	65	39	E3	PC8	I/O	FT	PC8	TIM3_CH3/LCD_SEG26/ SDIO_D0	-
99	D12	66	40	D1	PC9	I/O	FT	PC9	TIM3_CH4/LCD_SEG27/ SDIO_D1	-

## Table 8. STM32L151xD and STM32L152xD pin definitions (continued)



			Ta	able 9. A	Iternate	function	input/o	utput (conti	nued)				
					[	Digital alte	ernate fu	nction numb	er				
	AFIO0	AFIO1	AFIO2	AFIO3	AFIO4	AFIO5	AFIO6	AFIO7	AFIO8	AFIO11	AFIO12	AFIO14	AFIO15
Port name						Alt	ternate fu	unction	II		II_I		
	SYSTEM	TIM2	TIM3/4/5	TIM9/ 10/11	I2C1/2	SPI1/2	SPI3	USART1/2/3	UART4/5	LCD	FSMC/ SDIO	CPRI	SYSTEM
PG5	-	-	-	-	-	-	-	-	-	-	A15	-	EVENT OUT
PG6	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PG7	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PG8	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PG9	-	-	-	-	-	-	-	-	-	-	NE2	-	EVENT OUT
PG10	-	-	-	-	-	-	-	-	-	-	NE3	-	EVENT OUT
PG11	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PG12	-	-	-	-	-	-	-	-	-	-	NE4	-	EVENT OUT
PG13	-	-	-	-	-	-	-	-	-	-	A24	-	EVENT OUT
PG14	-	-	-	-	-	-	-	-	-	-	A25	-	EVENT OUT
PG15	-	-	-	-	-	-	-	-	-	-	-	-	EVENT OUT
PH0OSC_IN	-	-	-	-	-	-	-	-	-	-	-	-	-
PH1OSC_OUT	-	-	-	-	-	-	-	-	-	-	-	-	-
PH2	-	-	-	-	-	-	-	-	-	-	A22	-	-

Pin descriptions

5

Symbol	Parameter	Conditions		f <sub>HCLK</sub> [MHz]	Тур	Max (1)	Unit
			Range3.	1	290	500	
			V <sub>CORE</sub> =1.2 V	2	505	750	μA
		fuer = fuery up to 16MHz.	VOS[1:0]=11	4	955	1200	
			Range2.	4	1.15	1.6	
I <sub>DD (Run</sub>		included $f_{HSE} = f_{HCLK}/2$ above	V <sub>CORE</sub> =1.5 V	8	2.3	2.9	
		16 MHZ (PLL ON) <sup>(2)</sup>	VOS[1:0]=10	16	4.25	5.2	
			Range1,	8	2.65	3.5	
	Supply current in Run mode code executed from Flash		V <sub>CORE</sub> =1.8 V	16	5.35	6.5	
from			VOS[1:0]=01	32	10.5	12	μA
Flash) 6			Range2, V <sub>CORE</sub> =1.5 V VOS[1:0]=10	16	4.35	5.2	
		HSI CIOCK SOURCE (16 MHZ)	Range1, V <sub>CORE</sub> =1.8 V VOS[1:0]=01	32	10.5	12.3	
		MSI clock, 65 kHZ	Range3	0.065	46	130	
		MSI clock, 524 kHZ	V <sub>CORE</sub> =1.2 V	0.524	160	250	
		MSI clock, 4.2 MHZ	VOS[1:0]=11	4.2	965	1200	

#### Table 17. Current consumption in Run mode, code with data processing running from Flash

1. Guaranteed by characterization results, unless otherwise specified.

2. Oscillator bypassed (HSEBYP = 1 in RCC\_CR register).



		-				
		Typical o	onsumption,	V <sub>DD</sub> = 3.0 V, T	A = 25 °C	
Peripheral		Range 1, V <sub>CORE</sub> = 1.8 V VOS[1:0] = 01	Range 2, V <sub>CORE</sub> = 1.5 V VOS[1:0] = 10	Range 3, V <sub>CORE</sub> = 1.2 V VOS[1:0] = 11	Low-power sleep and run	Unit
I <sub>DD (RTC)</sub>						
I <sub>DD (LCD)</sub>						
I <sub>DD (ADC)</sub> <sup>(4)</sup>						
I <sub>DD (DAC)</sub> <sup>(5)</sup>						
I <sub>DD (COMP1)</sub>			μA			
1	Slow mode					
DD (COMP2)	Fast mode					
I <sub>DD (PVD / BOR</sub>	(6) )					
I <sub>DD (IWDG)</sub>			25			

lable 24. Peripheral current consumption ( ( continued	Table 24.	Peripheral	current	consumption <sup>(1)</sup>	(continued
--	-----------	------------	---------	----------------------------	------------

 Data based on differential I<sub>DD</sub> measurement between all peripherals OFF an one peripheral with clock enabled, in the following conditions: f<sub>HCLK</sub> = 32 MHz (range 1), f<sub>HCLK</sub> = 16 MHz (range 2), f<sub>HCLK</sub> = 4 MHz (range 3), f<sub>HCLK</sub> = 64kHz (Low-power run/sleep), f<sub>APB1</sub> = f<sub>HCLK</sub>, f<sub>APB2</sub> = f<sub>HCLK</sub>, default prescaler value for each peripheral. The CPU is in Sleep mode in both cases. No I/O pins toggling.

2. HSI oscillator is OFF for this measure.

- 3. In Low-power sleep and run mode, the Flash memory must always be in power-down mode.
- 4. Data based on a differential IDD measurement between ADC in reset configuration and continuous ADC conversion (HSI consumption not included).
- Data based on a differential IDD measurement between DAC in reset configuration and continuous DAC conversion of VDD/2. DAC is in buffered mode, output is left floating.
- 6. Including supply current of internal reference voltage.

#### 6.3.5 Wakeup time from low-power mode

The wakeup times given in the following table are measured with the MSI RC oscillator. The clock source used to wake up the device depends on the current operating mode:

- Sleep mode: the clock source is the clock that was set before entering Sleep mode
- Stop mode: the clock source is the MSI oscillator in the range configured before entering Stop mode
- Standby mode: the clock source is the MSI oscillator running at 2.1 MHz

All timings are derived from tests performed under the conditions summarized in Table 13.



# Multi-speed internal (MSI) RC oscillator

		acteristics				
Symbol	Parameter	Condition	Тур	Мах	Unit	
		MSI range 0	65.5	-		
		MSI range 1	131	-	kH-	
		MSI range 2	262	-	KI IZ	
f <sub>MSI</sub>	Frequency after factory calibration, done at $V_{DD}$ = 3.3 V and T <sub>A</sub> = 25 °C	MSI range 3	524	-		
		MSI range 4	1.05	-		
		MSI range 5	2.1	-	MHz	
		MSI range 6	4.2	-		
ACC <sub>MSI</sub>	Frequency error after factory calibration	-	±0.5	-	%	
D <sub>TEMP(MSI)</sub> <sup>(1)</sup>	MSI oscillator frequency drift 0 °C ≤T <sub>A</sub> ≤105 °C	-	±3	-	%	
D <sub>VOLT(MSI)</sub> <sup>(1)</sup>	MSI oscillator frequency drift 1.65 V ≤V <sub>DD</sub> ≤3.6 V, T <sub>A</sub> = 25 °C	-	-	2.5	%/V	
		MSI range 0	0.75	-		
		MSI range 1	1	-		
		MSI range 2	1.5	-		
I <sub>DD(MSI)</sub> <sup>(2)</sup>	MSI oscillator power consumption	MSI range 3	2.5	-	μA	
		MSI range 4	4.5	-		
		MSI range 5	8	-		
		MSI range 6	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$			
		MSI range 0	30	-		
		MSI range 1	20	-		
		MSI range 2	15	-		
		MSI range 3	10	-		
+	MSL oscillator startun timo	MSI range 4	6	-		
<sup>I</sup> SU(MSI)		MSI range 5	5	-	μs	
		MSI range 6, Voltage range 1 and 2	3.5	-		
		MSI range 6, Voltage range 3	5	-		

## Table 32. MSI oscillator characteristics



## Flash memory and data EEPROM

Symbol	Parameter	Conditions	Min	Тур	Max <sup>(1)</sup>	Unit
$V_{DD}$	Operating voltage Read / Write / Erase	-	1.65	-	3.6	V
t <sub>prog</sub>	Programming/ erasing	Erasing	-	3.28	3.94	
	time for byte / word / double word / half-page	Programming	-	3.28	3.94	ms
I <sub>DD</sub>	Average current during the whole programming / erase operation		-	600	900	μA
	Maximum current (peak) during the whole programming / erase operation	T <sub>A</sub> = 25 °C, V <sub>DD</sub> = 3.6 V	-	1.5	2.5	mA

Table 35. Flash memory and data EEPROM characteristics

1. Guaranteed by design.

Symbol	Deremeter	Conditions	\		Unit	
Symbol	Parameter	Conditions	Min <sup>(1)</sup>	Тур	Max	Unit
N. (2)	Cycling (erase / write) Program memory	$T_A = -40^{\circ}C$ to	10	-	-	kcycles
INCYC .	Cycling (erase / write) EEPROM data memory	105 °C	300	-	-	
	Data retention (program memory) after 10 kcycles at T <sub>A</sub> = 85 °C	T = +85 °C	30	-	-	
+ (2)	Data retention (EEPROM data memory) after 300 kcycles at $T_A$ = 85 °C	TRET - 103 C	30	-	-	voars
<sup>I</sup> RET <sup>(-)</sup>	Data retention (program memory) after 10 kcycles at T <sub>A</sub> = 105 °C	T = +105 °C	10	-	-	years
	Data retention (EEPROM data memory) after 300 kcycles at $T_A = 105 \text{ °C}$	1 <sub>RET</sub> = 1105 C	10	-	-	

Table 36, Flash memor	v and data EEPROM	endurance and retention
	$\mathbf{y}$ and data LET ROM	chautance and retention

1. Guaranteed by characterization results.

2. Characterization is done according to JEDEC JESD22-A117.



Symbol	Parameter	Min	Мах	Unit
t <sub>w(NE)</sub>	FSMC_NE low time	4*T <sub>HCLK</sub> - 3	4*T <sub>HCLK</sub> + 2	ns
t <sub>v(NWE_NE)</sub>	FSMC_NEx low to FSMC_NWE low	T <sub>HCLK</sub>	T <sub>HCLK</sub> + 1	ns
t <sub>w(NWE)</sub>	FSMC_NWE low time	2*T <sub>HCLK</sub> - 2	2*T <sub>HCLK</sub> + 4	ns
t <sub>h(NE_NWE)</sub>	FSMC_NWE high to FSMC_NE high hold time	T <sub>HCLK</sub> - 2.5	-	ns
t <sub>v(A_NE)</sub>	FSMC_NEx low to FSMC_A valid	-	6	ns
t <sub>v(NADV_NE)</sub>	FSMC_NEx low to FSMC_NADV low	1.5	2	ns
t <sub>w(NADV)</sub>	FSMC_NADV low time	T <sub>HCLK</sub> - 4	T <sub>HCLK</sub> + 4	ns
t <sub>h(AD_NADV)</sub>	FSMC_AD (address) valid hold time after FSMC_NADV high	T <sub>HCLK</sub> - 5	-	ns
t <sub>h(A_NWE)</sub>	Address hold time after FSMC_NWE high	T <sub>HCLK</sub> - 2.5	-	ns
t <sub>h(BL_NWE)</sub>	FSMC_BL hold time after FSMC_NWE high	T <sub>HCLK</sub> - 3	-	ns
t <sub>v(BL_NE)</sub>	FSMC_NEx low to FSMC_BL valid	-	0.5	ns
t <sub>v(Data_NADV)</sub>	FSMC_NADV high to Data valid	-	T <sub>HCLK</sub> + 6	ns
t <sub>h(Data_NWE)</sub>	Data hold time after FSMC_NWE high	T <sub>HCLK</sub> - 2.5	-	ns

Table 40. Asynchronous multiplexed PSRAM/NOR write timings<sup>(1)</sup>

1. C<sub>L</sub> = 30 pF.



## 6.3.14 I/O port characteristics

#### General input/output characteristics

Unless otherwise specified, the parameters given in *Table 56* are derived from tests performed under the conditions summarized in *Table 13*. All I/Os are CMOS and TTL compliant.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V <sub>IL</sub>	Input low level voltage	-	-	-	0.3V <sub>DD</sub>		
		Standard I/O		-	-		
$V_{\text{IH}}$	Input high level voltage	FT I/O	0.7 V <sub>DD</sub>	-	-	V	
		BOOT0 I/O		-	-		
V <sub>hys</sub>	I/O Schmitt trigger voltage hysteresis <sup>(2)</sup>	Standard I/O	-	10% V <sub>DD</sub> <sup>(3)</sup>	-		
I <sub>lkg</sub> I		V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> I/Os with LCD	-	-	±50		
	Input leakage current <sup>(4)</sup>	V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> I/Os with analog switches	-	-	±50		
		Input leakage current <sup>(4)</sup>	V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> I/Os with analog switches and LCD	-	-	±50	nA
		V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> I/Os with USB	-	-	±250		
		V <sub>SS</sub> ≤V <sub>IN</sub> ≤V <sub>DD</sub> Standard I/Os	-	-	±50		
		FT I/O V <sub>DD</sub> ≤ V <sub>IN</sub> ≤ 5V	-	-	±10	uA	
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(1)(5)</sup>	$V_{IN} = V_{SS}$	30	45	60	kΩ	
R <sub>PD</sub>	Weak pull-down equivalent resistor <sup>(5)</sup>	$V_{IN} = V_{DD}$	30	45	60	kΩ	
C <sub>IO</sub>	I/O pin capacitance	-	-	5	-	pF	

Table 50. I/O static characteristics

1. Guaranteed by test in production

2. Hysteresis voltage between Schmitt trigger switching levels. Guaranteed by characterization results.

3. With a minimum of 200 mV. Guaranteed by characterization results.

4. The max. value may be exceeded if negative current is injected on adjacent pins.

5. Pull-up and pull-down resistors are designed with a true resistance in series with a switchable PMOS/NMOS.







## 6.3.15 NRST pin characteristics

The NRST pin input driver uses CMOS technology. It is connected to a permanent pull-up resistor,  $R_{PU}$  (see *Table 53*)

Unless otherwise specified, the parameters given in *Table 53* are derived from tests performed under the conditions summarized in *Table 13*.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>IL(NRST)</sub> <sup>(1)</sup>	NRST input low level voltage	-	-	-	0.3 V <sub>DD</sub>	
V <sub>IH(NRST)</sub> <sup>(1)</sup>	NRST input high level voltage	-	0.7 V <sub>DD</sub>	-	-	V
	NRST output low	I <sub>OL</sub> = 2 mA 2.7 V < V <sub>DD</sub> < 3.6 V	-	-	0.4	v
VOL(NRST)`´	level voltage	I <sub>OL</sub> = 1.5 mA 1.65 V < V <sub>DD</sub> < 2.7 V	-	-	0.4	
V <sub>hys(NRST)</sub> <sup>(1)</sup>	NRST Schmitt trigger voltage hysteresis	-	-	10%V <sub>DD</sub> <sup>(2)</sup>	-	mV
R <sub>PU</sub>	Weak pull-up equivalent resistor <sup>(3)</sup>	$V_{IN} = V_{SS}$	30	45	60	kΩ
V <sub>F(NRST)</sub> <sup>(1)</sup>	NRST input filtered pulse	-	-	-	50	ns
V <sub>NF(NRST)</sub> <sup>(3)</sup>	NRST input not filtered pulse	out not		-	-	ns

Table 53. NRST pin characteristics

1. Guaranteed by design.

2. With a minimum of 200 mV.

3. The pull-up is designed with a true resistance in series with a switchable PMOS. This PMOS contribution to the series resistance is around 10%.



## 6.3.19 12-bit ADC characteristics

Unless otherwise specified, the parameters given in *Table 64* are guaranteed by design.

Symbol	Parameter		Conditions				Unit
f <sub>ADC</sub> ADC clock frequency		2.4 V ≤V <sub>DDA</sub> ≤3.6 V	V <sub>REF+</sub> = V <sub>DDA</sub>		16		
	Voltage ck range 1 & 2 cy		V <sub>REF+</sub> < V <sub>DDA</sub> V <sub>REF+</sub> > 2.4 V	0.480	8		
			V <sub>REF+</sub> < V <sub>DDA</sub> V <sub>REF+</sub> ≤2.4 V		4	MHz	
			V <sub>REF+</sub> = V <sub>DDA</sub>		8		
			1.0 V ≤V <sub>DDA</sub> ≤.4 V	V <sub>REF+</sub> < V <sub>DDA</sub>		4	
			Voltage range 3			4	

Table	63.	ADC	clock	frea	uencv
	•••		0.00.		

#### Table 64. ADC characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
V <sub>DDA</sub>	Power supply	-	1.8	-	3.6		
V <sub>REF+</sub>	Positive reference voltage	-	1.8 <sup>(1)</sup>	-	V <sub>DDA</sub>	V	
V <sub>REF-</sub>	Negative reference voltage	-	-	V <sub>SSA</sub>	-		
I <sub>VDDA</sub>	Current on the V <sub>DDA</sub> input pin	-	-	1000	1450		
ı (2)	Current on the V input nin	Peak	-	400	700	μΑ	
VREF <sup>(-)</sup>	Current on the v <sub>REF</sub> input pin	Average	-	400	450		
V <sub>AIN</sub>	Conversion voltage range <sup>(3)</sup>	-	0 <sup>(4)</sup>	-	V <sub>REF+</sub>	V	
	12 hit compling rate	Direct channels	-	-	1	Mene	
	12-bit Sampling rate	Multiplexed channels	-	-	0.76	wsps	
	10 hit compling rate	Direct channels	-	-	1.07	Mono	
f	TO-bit sampling rate	Multiplexed channels	-	-	0.8	ivisps	
IS	9 hit compling rate	Direct channels	-	-	1.23	Mana	
	o-bit sampling rate	Multiplexed channels	-	-	0.89	Msps	
	6 bit compling rate	Direct channels	-	-	1.45	Mono	
	o-bit sampling rate	Multiplexed channels	-	-	1	ivisps	



Symbol	Parameter	Conditions	Min	Тур	Мах	Unit	
dOffeet/dT <sup>(1)</sup>	Offset error temperature	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0V$ $T_A = 0 \text{ to } 50 \ ^{\circ}\text{C}$ DAC output buffer OFF	-20	-10	0	uV/°C	
donsetar	coefficient (code 0x800)	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0V$ $T_A = 0 \text{ to } 50 \ ^{\circ}\text{C}$ DAC output buffer ON	0	20	50	μν/ C	
	Cain array(7)	$C_{L} \le 50 \text{ pF}, R_{L} \ge 5 \text{ k}\Omega$ DAC output buffer ON	-	+0.1 / -0.2%	+0.2 / -0.5%	0/	
Gain	Gain error**	No R <sub>L</sub> , C <sub>L</sub> $\leq$ 50 pF DAC output buffer OFF	-	+0 / -0.2%	+0 / -0.4%	%	
dGain/dT <sup>(1)</sup>	Gain error temperature	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0V$ $T_A = 0 \text{ to } 50 \degree C$ DAC output buffer OFF	-10	-2	0	W//°C	
	coefficient	$V_{DDA} = 3.3V$ $V_{REF+} = 3.0V$ $T_A = 0 \text{ to } 50 ^{\circ}\text{C}$ DAC output buffer ON	-40	-8	0	μvi c	
TU⊏(1)	Total upadiustod orror	$C_L \le 50 \text{ pF}, R_L \ge 5 \text{ k}\Omega$ DAC output buffer ON	-	12	30		
		No R <sub>L</sub> , C <sub>L</sub> $\leq$ 50 pF DAC output buffer OFF	-	8	12	LOD	
t <sub>SETTLING</sub>	Settling time (full scale: for a 12-bit code transition between the lowest and the highest input codes till DAC_OUT reaches final value ±1LSB	$C_L \le 50 \text{ pF}, R_L \ge 5 \text{ k}\Omega$	-	7	12	μs	
Update rate	Max frequency for a correct DAC_OUT change (95% of final value) with 1 LSB variation in the input code	$C_L \le 50 \text{ pF}, R_L \ge 5 \text{ k}\Omega$	-	-	1	Msps	
t <sub>wakeup</sub>	Wakeup time from off state (setting the ENx bit in the DAC Control register) <sup>(8)</sup>	$C_L \le 50 \text{ pF}, R_L \ge 5 \text{ k}\Omega$	-	9	15	μs	
PSRR+	V <sub>DDA</sub> supply rejection ratio (static DC measurement)	$C_L \le 50 \text{ pF}, R_L \ge 5 \text{ k}\Omega$	-	-60	-35	dB	

Table 67	DAC	characteristics	(continued)
----------	-----	-----------------	-------------

1. Data based on characterization results.

2. Connected between DAC\_OUT and  $\mathsf{V}_{\mathsf{SSA}}.$ 

3. Difference between two consecutive codes - 1 LSB.



Table 75. LQPF100, 14 x 14 mm, 100-pin low-profile quad flat package mechanical	
data (continued)	

Symbol	millimeters			inches <sup>(1)</sup>		
Symbol	Min	Тур	Мах	Min	Тур	Мах
E3	-	12.000	-	-	0.4724	-
е	-	0.500	-	-	0.0197	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	3.5°	7.0°	0.0°	3.5°	7.0°
CCC	-	-	0.080	-	-	0.0031

1. Values in inches are converted from mm and rounded to 4 decimal digits.





1. Dimensions are in millimeters.



## Marking of engineering samples

The following figure gives an example of topside marking orientation versus pin 1 identifier location.



#### Figure 48. LQFP64 10 x 10 mm, 64-pin low-profile quad flat package top view example

 Parts marked as "ES", "E" or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity





Figure 55. Thermal resistance suffix 6





## 7.6.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org.



# 9 Revision History

Date	Revision	Changes
03-Oct-2011	1	Initial release.
03-Feb-2012	2	<ul> <li>Status of the document changed (datasheet instead of preliminary data).</li> <li>Updated low power features on page 1.</li> <li>Removed references to devices with 256 KB of Flash memory.</li> <li>GPIOF replaced with GIOPH.</li> <li>Added SDIO in <i>Table 4: Ultra-low-power STM32L15xxD device features and peripheral counts: on page 12</i> and in <i>Table 19: ction input/output on page 86</i> (FSMC/SDIO instead of FSMC).</li> <li><i>Table 4: Ultra-low-power STM32L15xxD device features and peripheral counts: replaced STM32L15xWD device features and peripheral counts: replaced STM32L15xWD.</i></li> <li><i>Figure 1: Ultra-low-power STM32L162QD UFBGA132 ballout:</i> replaced STM32L15xWC/D with STM32L15xQD.</li> <li><i>Figure 3, Figure 4:</i> updated titles.</li> <li><i>Table 14: STM32L15xD pin definitions:</i> updated title, updated pins PF0, PF1, PH2, PF12, PF13, PF14, PF15, PG0, PG1, PG12, PG15, PD0, and PD1.</li> <li><i>Table 19: ction input/output:</i> Modified ction for PA13 and PA14; removed EVENT OUT for PH2.</li> <li><i>Figure 5: Memory map:</i> removed the text "APB memory space".</li> <li>Modified <i>Table 2: Functionalities depending on the operating power supply range on page 15.</i></li> <li><i>Table 18: Current consumption in Run mode, code with data processing running from RAM:</i> added footnote 3.</li> <li><i>Table 19: Current consumption in Sleep mode:</i> updated condition for f<sub>HSE;</sub> added footnote 3.</li> <li><i>Table 23: Typical and maximum current consumptions in Standby mode:</i> modified max values.</li> <li><i>Table 64: USB DC electrical characteristics:</i> removed two footno</li></ul>

## Table 82. Document revision history

